Abstracts

Characterization of thermal and frequency-dispersion effects in GaAs MESFET devices

J. Rodriguez-Tellez, T. Fernandez, A. Mediavilla and A. Tazon. "Characterization of thermal and frequency-dispersion effects in GaAs MESFET devices." 2001 Transactions on Microwave Theory and Techniques 49.7 (Jul. 2001 [T-MTT]): 1352-1355.

New simple and accurate measurement procedures that enable the dispersion and thermal effects in GaAs MESFETs to be observed independently are presented in this paper. The results indicate that the differences observed between the static and pulsed characteristics of the device are not solely due to thermal effects, as is sometimes thought. Electrical and thermal measurements also show the GaAs MESFET to take a relatively long time before the effect of self-heating manifests itself on the IV characteristics of the device.

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